

EAST - [10650600.wsp:1]

FileViewEditToolsWindowHelp

Drafts

Pending

Active

L1: (1313) magnetic near tunnel near junction or MTJ and photolithography and chan\$1

L2: (1318) magnetic near tunnel near junction or MTJ and chan\$1 and shape\$1

L3: (632) 2 and ferromagnetic and switch\$3

L4: (0) 2 and ferromagnetic and control\$3 near magnetic near switch\$3

L5: (0) (magnetic near tunnel near junction or MTJ) and MRAM and ferromagnetic and (control\$3 near

L6: (0) (magnetic near tunnel near junction or MTJ) and MRAM and ferromagnetic and switch\$3 and c...

L7: (2) (magnetic near tunnel near junction or MTJ) and MRAM and ferromagnetic and switch\$3 and c...

L8: (9) (magnetic near tunnel near junction or MTJ) and MRAM and switch\$3 and chan\$1 and shape\$1

L9: (9) (magnetic near tunnel near junction or MTJ) and MRAM and chan\$1 and shape\$1

L10: (9) (magnetic near tunnel near junction or MTJ) and MRAM and chan\$1 and shape\$1

L11: (64) 2 and photolithography and (ion-milling or ion near milling)

L12: (1) ("6242770") PH

L13: (1) ("6166948") PH

L14: (1) ("5757695") PH

L15: (1) ("6376260") PH

L16: (1) ("6005800") PH

Failed

(magnetic near tunnel near junction or MTJ) and MRAM and and switch\$3 and chan\$1 and shape\$1

Saved

S1: (1321) magnetic near tunnel near junction or MTJ and photolithography and (ion-milling ion ne...

S2: (52) S1 and chan

S3: (72) (magnetic near tunnel near junction or MTJ) and photolithography and (ion-milling ion ne...

S4: (0) (magnetic near tunnel near junction or MTJ) and photolithography and chan

S5: (63) (magnetic near tunnel near junction or MTJ) and chan

Favorites

Tagged (0)

UEIC

Queue

Trash

Search

Doc

US-PCRD00:USPAT:EPD

Blank

Default graphic

OR

Highlight all elements

(magnetic near tunnel near junction or MTJ) and MRAM and chan\$1

BPS form

ISAR form

Image

Text

HTML

	U	I	Document ID	Issue Date	Pages	Title	Current OR	Current XRef	
1	<input type="checkbox"/>	<input type="checkbox"/>	US 20040257868 A1	20041223	16	MAGNETIC RAM CELL DEVICE AND ARRAY ARCHITECTURE	365/173	365/171	
2	<input type="checkbox"/>	<input type="checkbox"/>	US 20040245547 A1	20041209	40	Ultra low-cost solid-state memory	257/200		
3	<input type="checkbox"/>	<input type="checkbox"/>	US 20040240265 A1	20041202	17	SEGMENTED WORD LINE ARCHITECTURE FOR CROSS POINT MAGNETIC RANDOM ACCESS MEMORY	365/171		
4	<input type="checkbox"/>	<input type="checkbox"/>	US 20040190359 A1	20040930	15	Apparatus and method for disturb-free programming of passive element memory cells	365/225.7		
5	<input type="checkbox"/>	<input type="checkbox"/>	US 20040179398 A1	20040916	31	Method for programming a three-dimensional memory array incorporating serial chain diode stack	365/185.03	257/E27.026; 257/E27.073	
6	<input type="checkbox"/>	<input type="checkbox"/>	US 20040178404 A1	20040916	17	Multiple bit chalcogenide storage device	257/4		

eDAN Versi...

EAST - [106...

EAST Brow...

EAST Brow...

7 Microso...